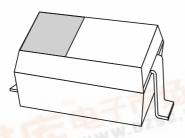
DISCRETE SEMICONDUCTORS

DATA SHEET



1PS76SB10 Schottky barrier diode

Product specification

1996 Oct 14







Schottky barrier diode

1PS76SB10

FEATURES

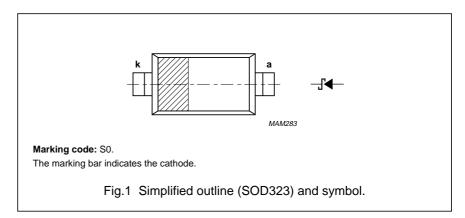
- Low forward voltage
- · Guard ring protected
- Very small plastic SMD package.

APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- · Protection circuits
- · Blocking diodes.

DESCRIPTION

Planar Schottky barrier diode encapsulated in a SOD323 very small plastic SMD package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage		_	30	V
I _F	continuous forward current		_	200	mA
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ s; } \delta \le 0.5$	_	300	mA
I _{FSM}	non-repetitive peak forward current	t _p < 10 ms	_	600	mA
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	125	°C
T _{amb}	operating ambient temperature		-65	+125	°C

2

1996 Oct 14

Philips Semiconductors Product specification

Schottky barrier diode

1PS76SB10

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.2		
		I _F = 0.1 mA	240	mV
		I _F = 1 mA	320	mV
		I _F = 10 mA	400	mV
		I _F = 30 mA	500	mV
		I _F = 100 mA	800	mV
I _R	reverse current	V _R = 25 V; note 1; see Fig.3	2	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; see Fig.4	10	pF

Note

1. Pulsed test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	450	K/W

Note

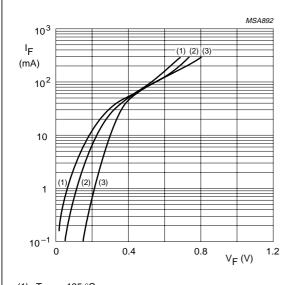
1. Refer to SOD323 standard mounting conditions.

1996 Oct 14 3

Schottky barrier diode

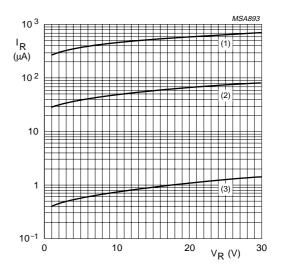
1PS76SB10

GRAPHICAL DATA



- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.

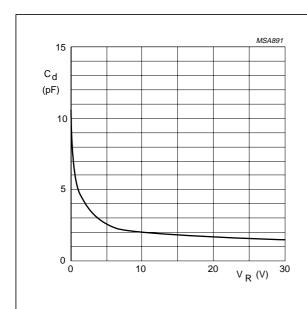


- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.

4

(3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

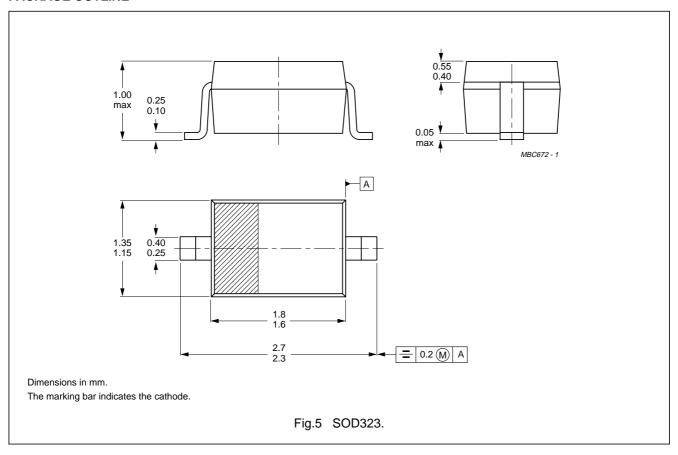
1996 Oct 14

Philips Semiconductors Product specification

Schottky barrier diode

1PS76SB10

PACKAGE OUTLINE



DEFINITIONS

Data sheet status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

1996 Oct 14 5